INFORMATION DISCLOSURE CITATION SEP 1 0 2007 (USA) several sheets if necessary)				APPLICANT(S): Takatoshi Tsujimura et FILING DATE:	CMO.0012US (P030096ATZLUS) APPLICANT(S): Takatoshi Tsujimura et al. FILING DATE: GROU		SERIAL NO. 10/693,244 UP ART UNIT:	
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*EXAMINER: I	Initial if refe	ference considered, whether or not cit	itation is in conformance v	with MPEP 609; Draw line through citation if		e and not consid	ered. Includi	в сору